

TYN625



单向可控硅
THYRISTOR

版本号
201603-A

产品概述 GENERAL DESCRIPTION

TYN625 单向可控硅采用穿通隔离台面结构，复合玻璃钝化PN结表面保护工艺技术，dv/dt高，可靠性高，适用于控温、调光、马达控制。

TYN625 Thyristor is fabricated using separation diffusion processes ,the junction termination areas are passivated with glass. Thanks to highly dv/dt and reliability,the Triacs series is suitable for domestic lighting ,heating and motor speed controllers.

主要参数 MAIN CHARACTERISTICS

参数 Parameter	数值 Value	单位 Unit
I _{T(RMS)}	25	A
V _{DRM/V_{RRM}}	600	V
I _{GT}	≤40	mA

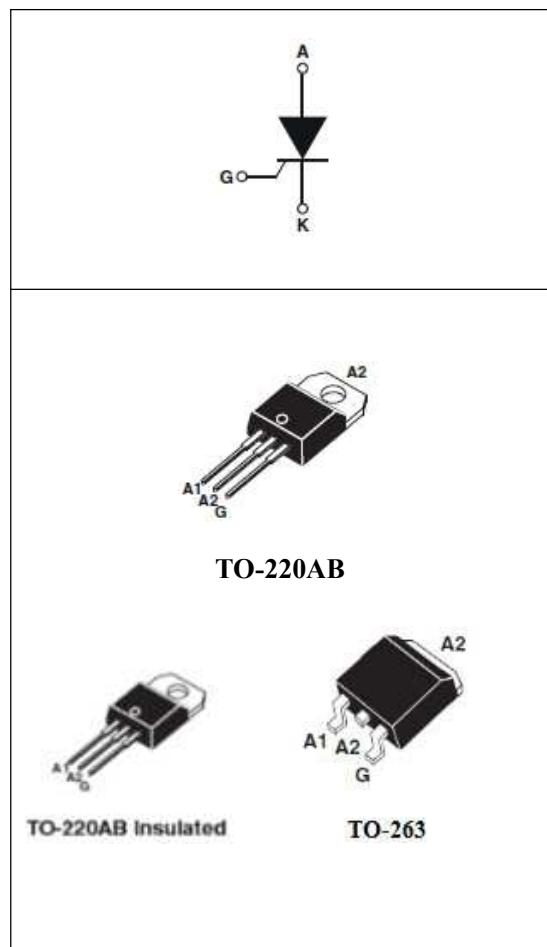
产品特性 FEATURES

- dv/dt高
- 通态压降低
- RoHS环保产品
- Highly dv/dt
- Low on-state voltage
- RoHS Products

应用领域 APPLICATIONS

主要应用于调光、控温、马达控制。

domestic lighting ,heating and motor speed controllers.



极限值(除非另有规定, $T_j=25^\circ\text{C}$) ABSOLUTE RATINGS

($T_j=25^\circ\text{C}$,unless otherwise specified)

符号 Symbol	参数 Parameter	数值 Value	单位 Unit	
I_{TRMS}	RMS 通态电流 RMS on-state current (full sine wave)	$T_c=100^\circ\text{C}$	25	A
I_{TSM}	通态峰值浪涌电流 Non repetitive surge peak on-state current	$F=50\text{Hz}, t=10\text{ms}$	300	A
I^2t	I^2t 耗散值 I^2t value for fusing	$T_p=10\text{ms}$	450	A^2s
di/dt	通态电流上升值 Critical rate of rise of on-state current	$F=60\text{Hz}, T_j=125^\circ\text{C}$	50	$\text{A}/\mu\text{s}$
I_{GM}	门极峰值电流 Peak gate current	$TP=20\mu\text{s}, T_j=125^\circ\text{C}$	3.5	A
$P_{G(AV)}$	平均门极耗散功率 Average gate power dissipation	$T_j=125^\circ\text{C}$	0.8	W
T_{stg}	贮存结温范围 Storage junction temperature range	-40-+150	$^\circ\text{C}$	
T_j	工作结温范围 Operating junction temperature range	-40-+125	$^\circ\text{C}$	

电参数(除非另有规定, $T_j=25^\circ\text{C}$) ELECTRICAL CHARACTERISTICS

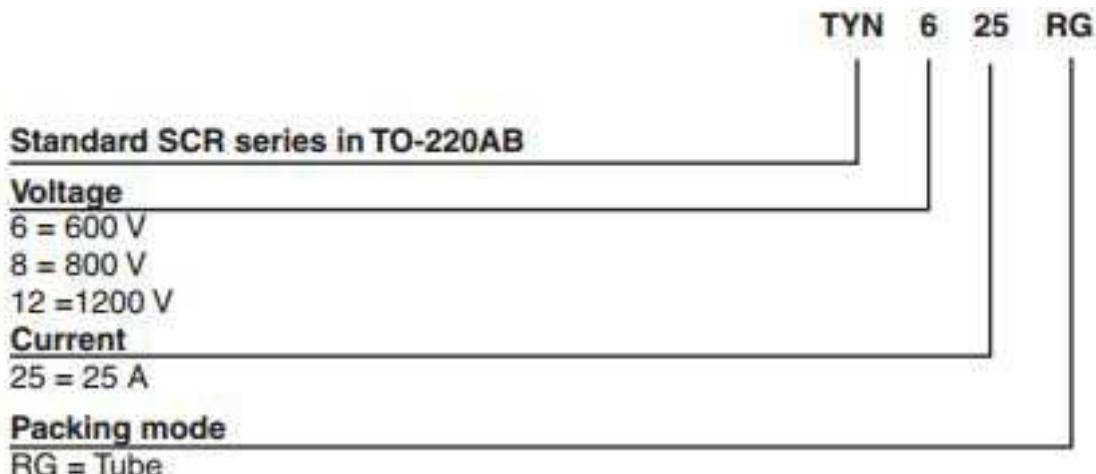
($T_j=25^\circ\text{C}$,unless otherwise specified)

参数 Parameter	符号 Symbol	规范值 Value	单位 Unit	测试条件 Test Conditions
触发电流 Gate trigger current	I_{GT}	≤ 40	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
触发电压 Gate trigger voltage	V_{GT}	≤ 1.5	V	$V_D=12\text{V}, I_T=0.1\text{A}$
维持电流 Holding current	I_H	≤ 50	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
擎住电流 Latching current	I_L	≤ 90	mA	$V_D=12\text{V}, I_T=0.1\text{A}$
电压上升率 Rise of off- state voltage	dv/dt	≥ 400	$\text{V}/\mu\text{s}$	$V_D=67\%V_{DRM}$
通态压降 Peak on-state voltage	V_{TM}	≤ 1.6	V	$I_T=50\text{A}$
断态漏电流 Peak repetitive forward blocking current	I_{DRM}	≤ 10	μA	$V_{RRM}=V_{DRM}, T_j=25^\circ\text{C}$
	I_{RRM}	≤ 4	mA	$V_{RRM}=V_{DRM}, T_j=125^\circ\text{C}$

热特性 THERMAL RESISTANCES

符号 Symbol	参数 Parameter		数值 Value	单位 Unit
Rth(j-c)	Junction to case(AC)	TO-220AB	1.4	°C/W
		TO-220AB Insulated	2.5	
		TO-263	0.8	
Rth(j-a)	Junction to ambient	TO-220AB	60	°C/W
		TO-220AB Insulated	60	
		TO-263	45	

ORDERING INFORMATION



特征曲线 ELECTRICAL CHARACTERISTICS (CURVES)

图1 最大耗散功率与平均通态电流关系
Fig.1. Maximum Power Dissipation Versus
Average on-state current

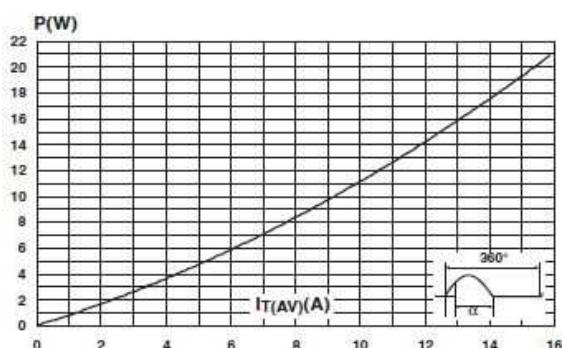


图3 通态特性
Fig.3.On-State Characteristics

图2 平均通态电流与Tc温度关系
Fig.2. IT_(AV) On-state Current Versus TL

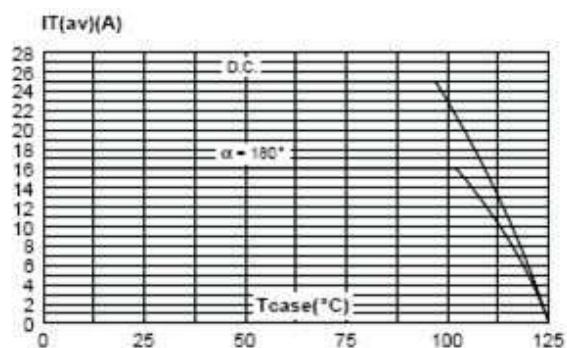


图4 通态浪涌峰值电流与周期数关系
Fig.4.Surge Peak On-state Current Versus Number Cycles

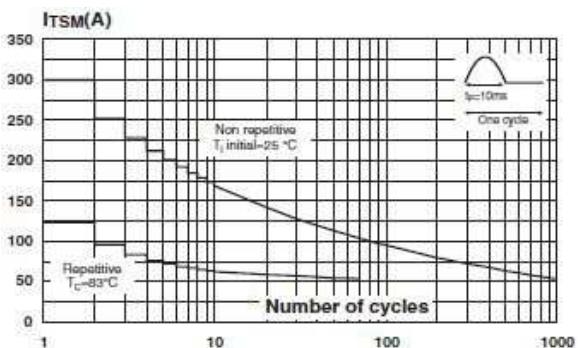
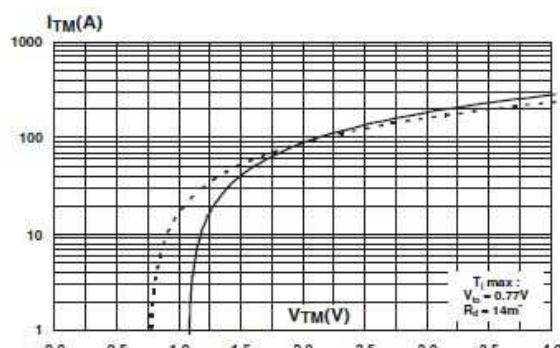
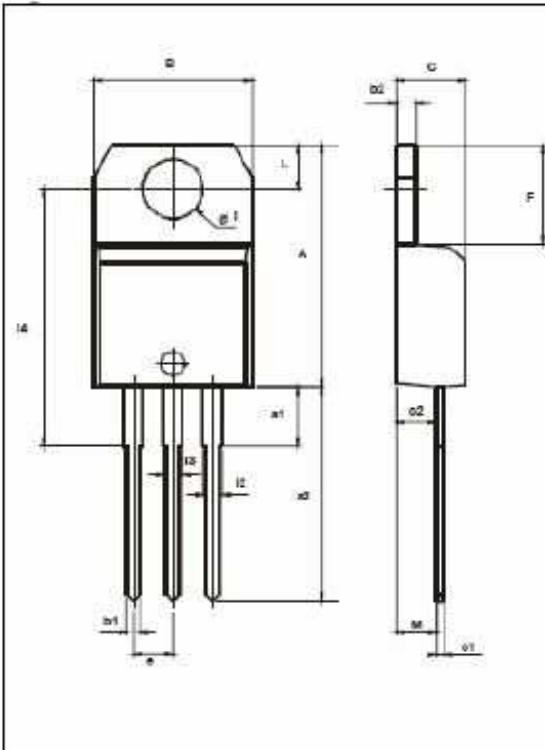


图5 IGT、IH、IL相对值（相对于25°C）与结温关系
Fig.5.Relative Variation Of Gate Trigger Current
, Holding Current And Latching Current Versus Junction Temperature (Typical Value)

封装尺寸 PACKAGE MECHANICAL DATA

TO-220AB AND TO-220AB Insulated



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.20		15.90	0.598		0.625
a1		3.75			0.147	
a2	13.00		14.00	0.511		0.551
B	10.00		10.40	0.393		0.409
b1	0.61		0.88	0.024		0.034
b2	1.23		1.32	0.048		0.051
C	4.40		4.60	0.173		0.181
c1	0.49		0.70	0.019		0.027
c2	2.40		2.72	0.094		0.107
e	2.40		2.70	0.094		0.105
F	6.20		6.60	0.244		0.259
I	3.75		3.85	0.147		0.151
I4	15.80	16.40	16.80	0.622	0.646	0.661
L	2.65		2.95	0.104		0.116
I2	1.14		1.70	0.044		0.066
I3	1.14		1.70	0.044		0.066
M		2.60			0.102	

TO-263

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.70		0.93	0.027		0.037
B2	1.25	1.40		0.048	0.055	
C	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	8.95		9.35	0.352		0.368
E	10.00		10.28	0.393		0.405
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.40	0.050		0.055
L3	1.40		1.75	0.055		0.069
R	0.40			0.016		
V2	0°		8°	0°		8°

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